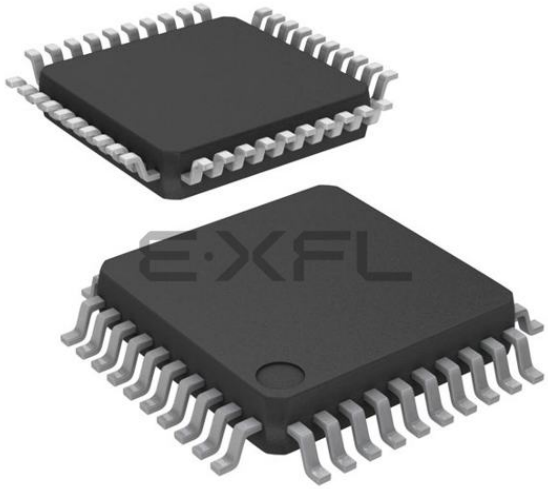
Renesas Electronics America Inc - R5F21336CNFP#X6 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	27
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21336cnfp-x6

1.1.2 Specifications

Tables 1.1 and 1.2 outline the Specifications for R8C/33C Group.

Table 1.1 Specifications for R8C/33C Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C CPU core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 1.8 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM, Data flash	Refer to **Table 1.3 Product List for R8C/33C Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3 (detection level of voltage detection 0 and voltage detection 1 selectable)
I/O Ports	Programmable I/O ports	• Input-only: 1 pin • CMOS I/O ports: 27, selectable pull-up resistor • High current drive ports: 27
Clock	Clock generation circuits	4 circuits: XIN clock oscillation circuit, XCIN clock oscillation circuit (32 kHz), High-speed on-chip oscillator (with frequency adjustment function), Low-speed on-chip oscillator • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• Number of interrupt vectors: 69 • External Interrupt: 7 ($\overline{\text{INT}}$ × 3, Key input × 4) • Priority levels: 7 levels
Watchdog Timer		• 14 bits × 1 (with prescaler) • Reset start selectable • Low-speed on-chip oscillator for watchdog timer selectable
DTC (Data Transfer Controller)		• 1 channel • Activation sources: 23 • Transfer modes: 2 (normal mode, repeat mode)
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode

Table 1.2 Specifications for R8C/33C Group (2)

Item	Function	Specification
Serial Interface	UART0, UART1	Clock synchronous serial I/O/UART × 2 channel
	UART2	Clock synchronous serial I/O/UART, I²C mode (I²C-bus), multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I²C-bus)
I²C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 12 channels, includes sample and hold function, with sweep mode
D/A Converter		8-bit resolution × 2 circuits
Comparator B		2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • Background operation (BGO) function
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 1.8 to 5.5 V)
Current Consumption		Typ. 6.5 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 3.5 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) Typ. 2.0 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version) (1)
Package		32-pin LQFP Package code: PLQP0032GB-A (previous code: 32P6U-A)

Note:
1. Specify the D version if D version functions are to be used.

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

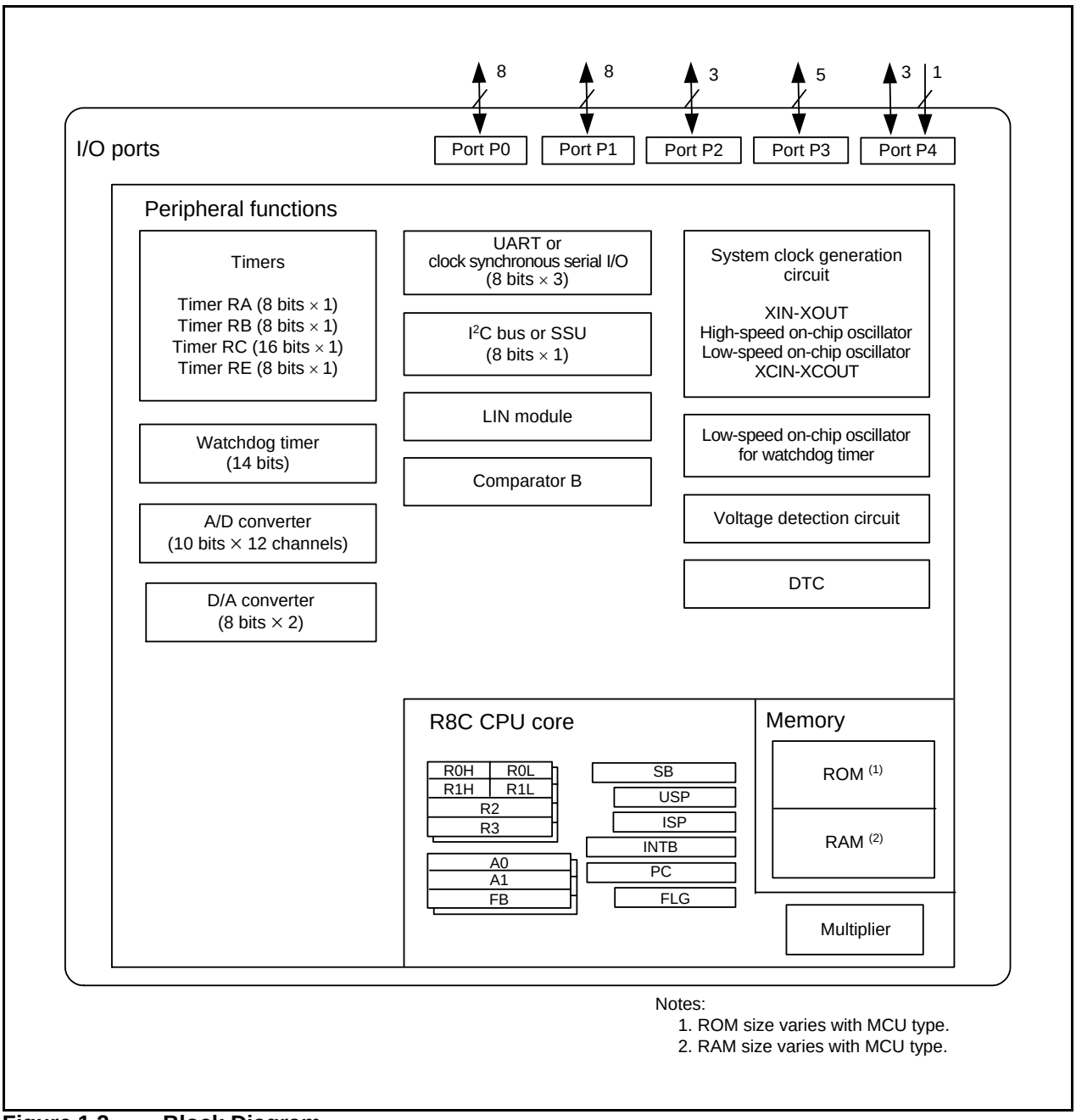


Figure 1.2 Block Diagram

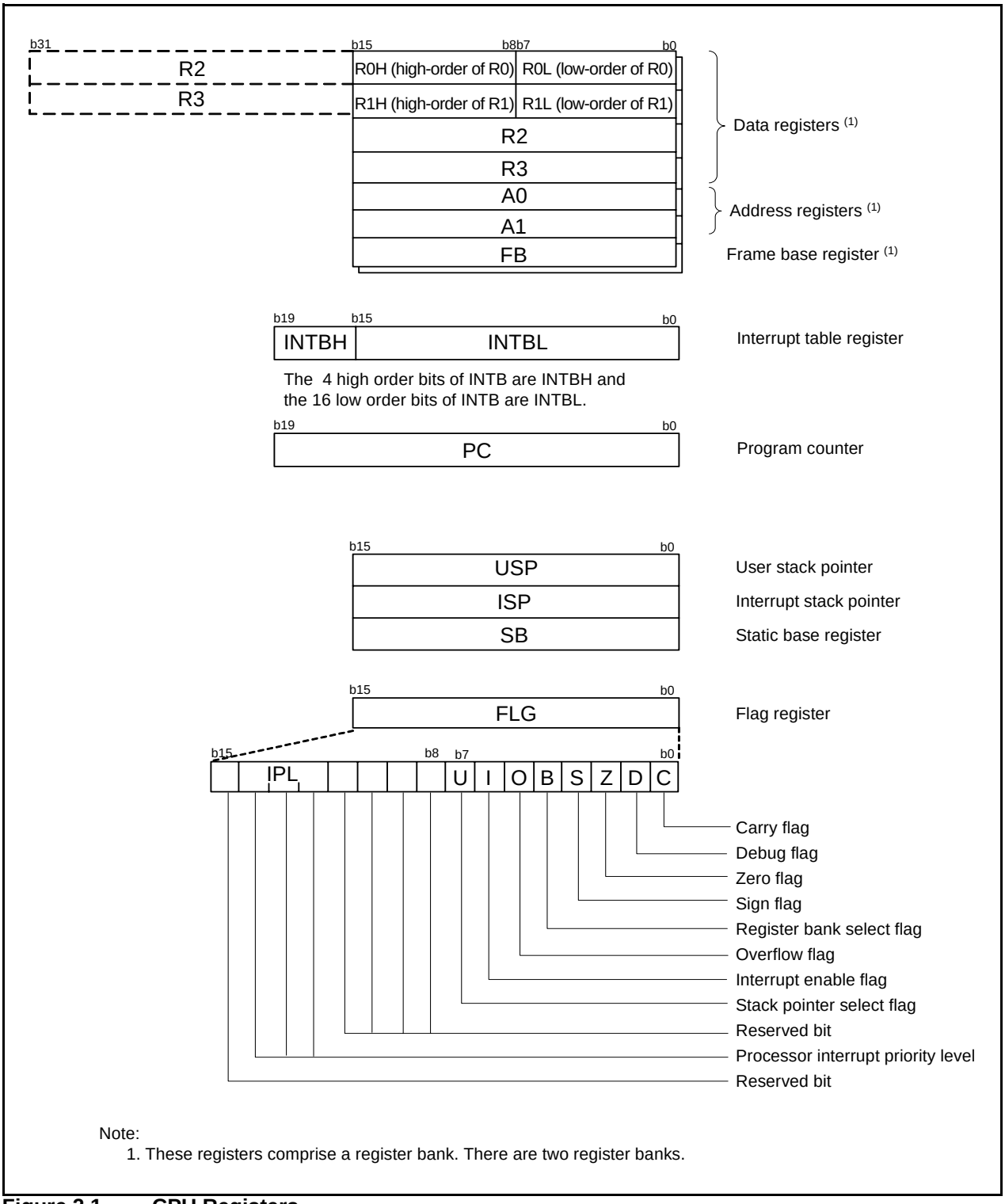
Table 1.4 Pin Name Information by Pin Number

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator B
1		P4_2						VREF
2	MODE							
3	$\overline{\text{RESET}}$							
4	XOUT(/XCOUT)	P4_7						
5	VSS/AVSS							
6	XIN(/XCIN)	P4_6						
7	VCC/AVCC							
8		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
9		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
10		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
11		P3_3	$\overline{\text{INT3}}$	(TRCCLK)	($\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$)	$\overline{\text{SCS}}$		IVCMP3
12		P2_2		(TRCIOD)				
13		P2_1		(TRCIOC)				
14		P2_0	($\overline{\text{INT1}}$)	(TRCIOB)				
15		P3_1		(TRBO)				
16		P4_5	$\overline{\text{INT0}}$		(RXD2/SCL2)			$\overline{\text{ADTRG}}$
17		P1_7	$\overline{\text{INT1}}$	(TRAIO)				IVCMP1
18		P1_6			(CLK0)			IVREF1
19		P1_5	($\overline{\text{INT1}}$)	(TRAIO)	(RXD0)			
20		P1_4		(TRCCLK)	(TXD0)			
21		P1_3	$\overline{\text{KI3}}$	TRBO (/TRCIOC)				AN11
22		P1_2	$\overline{\text{KI2}}$	(TRCIOB)				AN10
23		P1_1	$\overline{\text{KI1}}$	(TRCIOA/ TRCTRG)				AN9
24		P1_0	$\overline{\text{KI0}}$	(TRCIOD)				AN8
25		P0_7		(TRCIOC)				AN0/DA1
26		P0_6		(TRCIOD)				AN1/DA0
27		P0_5		(TRCIOB)				AN2
28		P0_4		TREO (/TRCIOB)				AN3
29		P0_3		(TRCIOB)	(CLK1)			AN4
30		P0_2		(TRCIOA/ TRCTRG)	(RXD1)			AN5
31		P0_1		(TRCIOA/ TRCTRG)	(TXD1)			AN6
32		P0_0		(TRCIOA/ TRCTRG)				AN7

Note:
1. Can be assigned to the pin in parentheses by a program.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



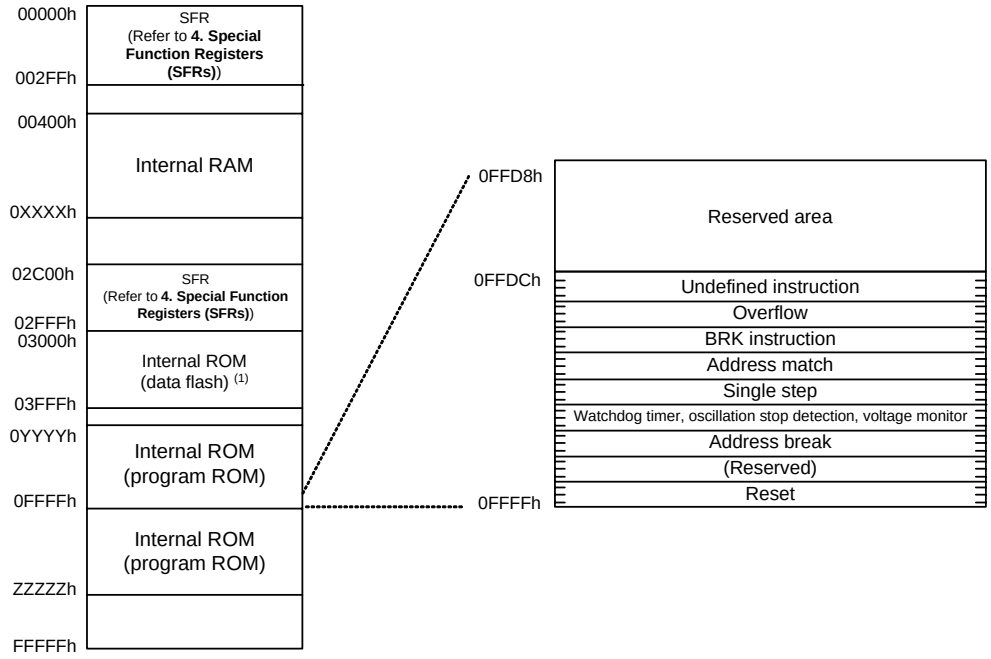
Note:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

3. Memory

3.1 R8C/33C Group

Figure 3.1 is a Memory Map of R8C/33C Group. The R8C/33C Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 32-Kbyte internal ROM area is allocated addresses 08000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. Data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21331CNFP, R5F21331CDFP	4 Kbytes	0F000h	–	512 bytes	005FFh
R5F21332CNFP, R5F21332CDFP	8 Kbytes	0E000h	–	1 Kbyte	007FFh
R5F21334CNFP, R5F21334CDFP	16 Kbytes	0C000h	–	1.5 Kbytes	009FFh
R5F21335CNFP, R5F21335CDFP	24 Kbytes	0A000h	–	2 Kbytes	00BFFh
R5F21336CNFP, R5F21336CDFP	32 Kbytes	08000h	–	2.5 Kbytes	00DFFh

Figure 3.1 Memory Map of R8C/33C Group

Table 4.12 SFR Information (12) (1)

Address	Register	Symbol	After Reset
2CF0h	DTC Control Data 22	DTCD22	XXh
2CF1h			XXh
2CF2h			XXh
2CF3h			XXh
2CF4h			XXh
2CF5h			XXh
2CF6h			XXh
2CF7h			XXh
2CF8h	DTC Control Data 23	DTCD23	XXh
2CF9h			XXh
2CFAh			XXh
2CFBh			XXh
2CFCh			XXh
2CFDh			XXh
2CFEh			XXh
2CFFh			XXh
2D00h			
:			
2FFFh			

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

Table 4.13 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
:			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
:			
FFDFh	ID1		(Note 2)
:			
FFE3h	ID2		(Note 2)
:			
FFEBh	ID3		(Note 2)
:			
FFEFh	ID4		(Note 2)
:			
FFF3h	ID5		(Note 2)
:			
FFF7h	ID6		(Note 2)
:			
FFFBh	ID7		(Note 2)
:			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:
1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh.
When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user.
When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh.
When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user.
When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}		–	–	10	Bit
–	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	20	MHz
			3.2 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	16	MHz
			2.7 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	10	MHz
			2.2 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	5	MHz
–	Tolerance level impedance				–	3	–	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
I_{Vref}	V_{ref} current		Vcc = 5 V, XIN = f1 = ϕAD = 20 MHz		–	45	–	µA
V_{ref}	Reference voltage				2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	–	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
–	Voltage detection 0 circuit response time (4)	At the falling of Vcc from 5 V to (Vdet0_0 – 0.1) V	–	6	150	µs
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	1.5	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of Vcc	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of Vcc	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of Vcc	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of Vcc	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of Vcc	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of Vcc	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of Vcc	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of Vcc	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of Vcc	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of Vcc	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of Vcc	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of Vcc	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of Vcc	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of Vcc	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of Vcc	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of Vcc	4.20	4.45	4.75	V
–	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	–	0.07	–	V
		Vdet1_6 to Vdet1_F selected	–	0.10	–	V
–	Voltage detection 1 circuit response time (3)	At the falling of Vcc from 5 V to (Vdet1_0 – 0.1) V	–	60	150	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.10 Voltage Detection 2 Circuit Electrical Characteristics

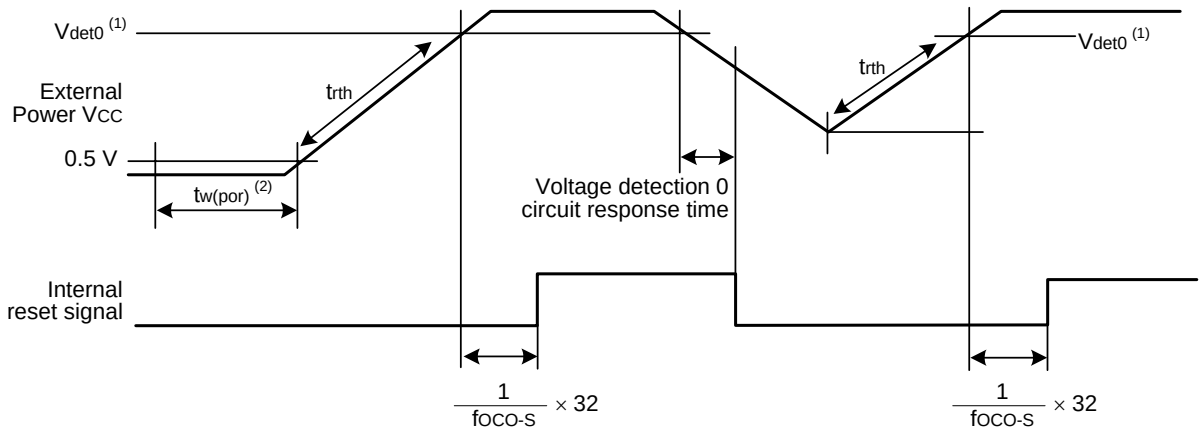
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0	At the falling of V_{CC}	3.70	4.00	4.30	V
–	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		–	0.10	–	V
–	Voltage detection 2 circuit response time (2)	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	20	150	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.11 Power-on Reset Circuit (2)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient	(1)	0	–	50,000	mV/msec

Notes:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of User's Manual: Hardware (REJ09B0570) for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	38.4	40	41.6	MHz
		V_{CC} = 1.8 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	35.389	36.864	38.338	MHz
		V_{CC} = 1.8 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	30.72	32	33.28	MHz
		V_{CC} = 1.8 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C	30.40	32	33.60	MHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	0.5	3	ms
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	400	–	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	30	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	2	–	µA

Note:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		–	–	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

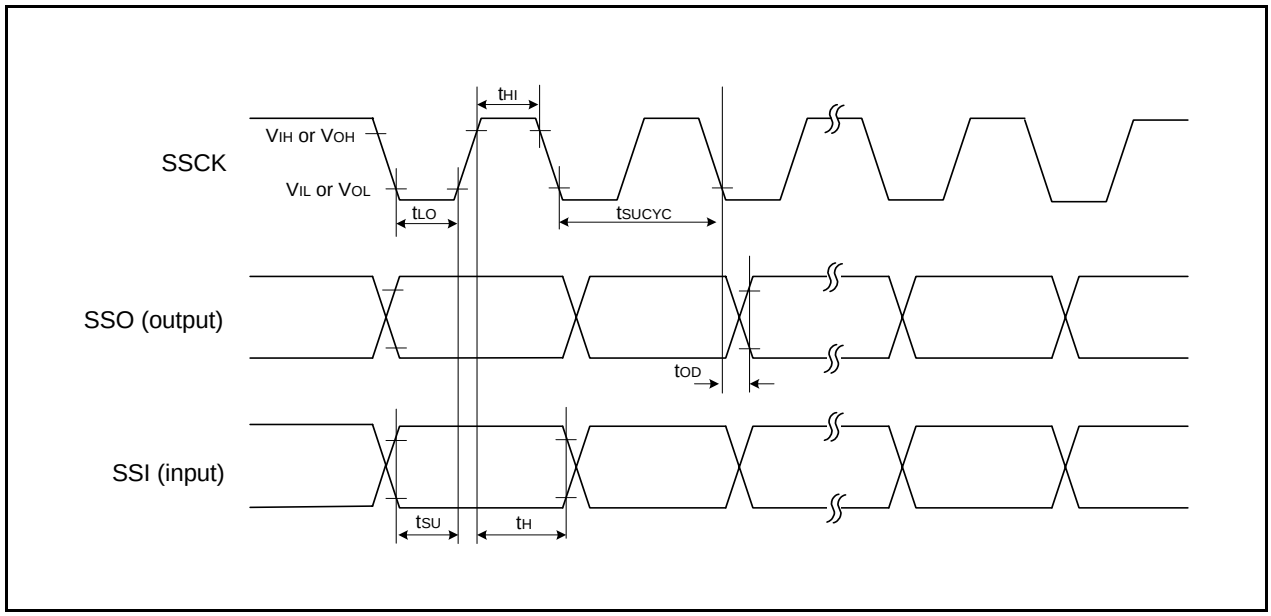
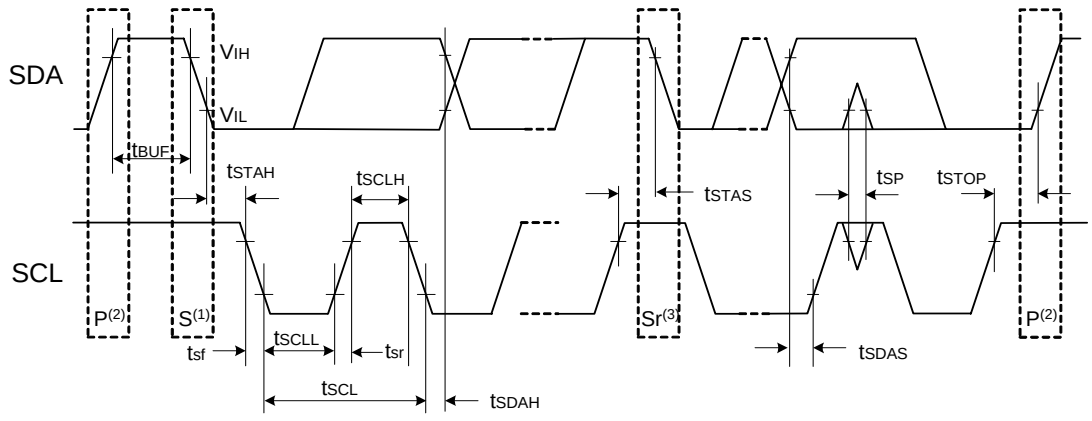


Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.16 Timing Requirements of I²C bus Interface (1)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC} + 600$ (2)	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC} + 300$ (2)	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC} + 500$ (2)	–	–	ns
t_{sf}	SCL, SDA input fall time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}$ (2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$ (2)	–	–	ns
t_{STAH}	Start condition input hold time		$3t_{CYC}$ (2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$ (2)	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$ (2)	–	–	ns
t_{SDAS}	Data input setup time		$1t_{CYC} + 40$ (2)	–	–	ns
t_{SDAH}	Data input hold time		10	–	–	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC} = 1/f1(s)$



Notes:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.7 I/O Timing of I²C bus Interface

Table 5.17 Electrical Characteristics (1) [4.2 V ≤ Vcc ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OH} = –20 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity Low V_{CC} = 5 V	I_{OH} = –5 mA	V_{CC} – 2.0	–	V_{CC}	V
		XOUT	V_{CC} = 5 V	I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity Low V_{CC} = 5 V	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	V_{CC} = 5 V	I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	1.2	–	V
		$\overline{RESET}$			0.1	1.2	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5.0 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5.0 V		–	–	–5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5.0 V		25	50	100	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 4.2 V ≤ V_{CC} ≤ 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.18 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.2	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	85	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	47	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.24 Electrical Characteristics (4) [2.7 V ≤ Vcc < 3.3 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Timing requirements
(Unless Otherwise Specified: Vcc = 3 V, Vss = 0 V at Topr = 25°C)

Table 5.25 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

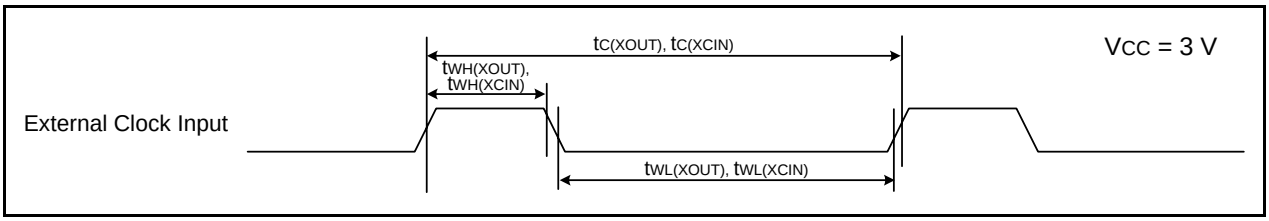


Figure 5.12 External Clock Input Timing Diagram when Vcc = 3 V

Table 5.26 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

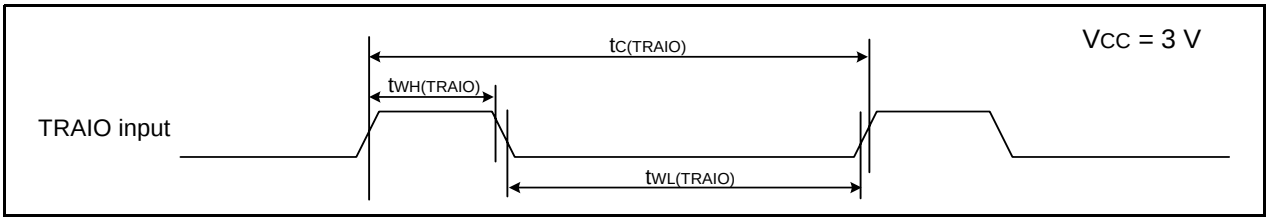


Figure 5.13 TRAIO Input Timing Diagram when Vcc = 3 V

Table 5.29 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.05	0.20	–	V
		$\overline{RESET}$			0.05	0.2	–	V
I_{IH}	Input “H” current		VI = 2.2 V, V_{CC} = 2.2 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 2.2 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 1.8 V ≤ V_{CC} < 2.7 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Table 5.30 Electrical Characteristics (6) [1.8 V ≤ Vcc < 2.7 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 1.8 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	2.2	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	0.8	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	2.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.7	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

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